Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"20040155244"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:12
S2	2	("6207586").PN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/17 15:16
S3	11	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S4	9	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'gate insulating' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:37
S5	198	@ad<="20040114" and 'monocrystalline silicon' and 'thermal oxide' same 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:31
S6	4	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'gate' with 'thermal oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:38
S7	22	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'gate insulating' and 'thermal oxide' and 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:52
S10	116	@ad<="20040114" and 'gate insulating' same 'thermal oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:52
S11	4	@ad<="20040114" and 'tft;' and 'monocrystalline silicon' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/05/17 15:54
S12	70	@ad<="20040114" and 'monocrystalline silicon' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:54

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S13	34	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 16:05
S14	112	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'oxidized'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:58
S15	1	"20030116719".PN.	US-PGPUB	OR	ON	2005/05/17 16:05
S16	1	"20030085397".PN.	US-PGPUB	OR	ON	2005/05/17 16:05
S17	138	@ad<="20040114" and 'LCD' and 'monocrystalline silicon' and 'oxide' same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 08:40
S18	15	@ad<="20040114" and 'electro-optical' and 'monocrystalline silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 08:40
S19	9	@ad<="20040114" and 'LCD' and 'monocrystalline silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 08:40
S20	131	@ad<="20040114" and 'LCD' and 'monocrystalline silicon' and 'oxide' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 08:40
S22		'wo 200011709'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 09:05
S23	1	"5432625".PN	USPAT; USOCR	OR	ON	2005/05/18 10:28
S24	3	@ad<="20040114" and 'TFT' and 'monocrystal' with 'silicon' and 'insulating' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/08/02 14:25
S25	102	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 11:23
S26	80	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide' and 'oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:58

S27	3	("6011275").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/18 11:52
S28	9251	@ad<="20040114" and (257/59). ccls. or (257/347).ccls. or (257/64). ccls. or (257/65).ccls. or (257/66). ccls. or (257/67).ccls. or (257/72). ccls. or (257/E21.413).ccls. or (257/E21.703).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 11:55
S29	704	@ad<="20040114".and (257/57). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:04
S30	1155	@ad<="20040114" and (257/79). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:04
S31	81	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide' and 'oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 14:26
S32	3	@ad<="20040114" and 'TFT' and 'monocrystal' with 'silicon' and 'insulating' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:02
S33	36	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide' and 'oxide' with 'cvd' and 'LDD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2005/12/06 08:20
S34	9	("6077731").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/02 14:58
S45	110	@ad<="20040114" and 'single crystal' with 'silicon' same 'mono'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:55
S46	81	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide' and 'oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:58

S47	855	@ad<="20040114" and 'TFT' and 'monocrystalline'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:02
S48	61	@ad<="20040114" and 'TFT' and 'monocrystalline' and 'gate' with 'thermal' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:05
S49	7	@ad<="20040114" and 'TFT' and 'monocrystalline' and 'gate' with 'thermal' with 'cvd' and 'ldd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/08/02 16:05
S50	38	@ad<="20040114" and 'TFT' and 'monocrystalline' and 'thermal' with 'cvd' and 'ldd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:05
S51	. 0	@ad<="20040114" and 'TFT' and 'insulating gate' with 'capacitor line'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:59
S52	183	@ad<="20040114" and 'TFT' and 'gate insulating' same 'capacitor line'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/08/03 08:00
S53	136	@ad<="20040114" and 'TFT' and 'gate insulating' with 'capacitor line'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 08:00
S54	31	@ad<="20040114" and 'TFT' with 'gate insulating' with 'capacitor line'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 08:00
S55	183	@ad<="20040114" and 'TFT' and ('monocrystalline' or 'monocrystall or 'crystallinity') with 'silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:57
S56	71	@ad<="20040114" and 'TFT' and ('monocrystalline' or 'monocrystall or 'crystallinity') with 'silicon' and 'thermal oxide' same 'cvd' same 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/11 09:58
S57		@ad<="20040114" and 'TFT' same 'monocrystalline' with 'silicon' and 'thermal oxide' same 'cvd' same 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:00

S58	8	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:02
S59	200	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:02
S60	128	@ad<="20040114" and 'TFT' with 'monocrystalline' with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:02
S61	111	@ad<="20040114" and 'TFT' with 'monocrystalline silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:07
S62	37	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' same 'channel' and 'LDD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:22
S63	8	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' same 'active layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:13
S64	0	@ad<="20040114" and 'TFT' same 'monocrystalline semiconductor' with 'active layer' same 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:13
S65	0	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'active layer' same 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/12/06 08:14
S66	0	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'active' same 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S67		@ad<="20040114" and 'TFT' and 'monocrystalline' with 'active' same 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S68		@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14

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S69	0	@ad<="20040114" and 'TFT' and 'monocrystalline' with 'active' and 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S70	8	@ad<="20040114" and 'TFT' and 'mono' with 'crystal' with 'silicon' and ('insulating' or 'dielectric') with 'thermal oxide' and ('oxide' or 'nitride') with 'cvd' and 'LDD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/12/06 08:21
S71	67	@ad<="20040114" and ("TFT" or "thin film transistor") and (monocrystal\$4 or "crystallinity") with silicon and "thermal oxide" same ("cvd" with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/11 10:01
S72	· 78	@ad<="20040114" and crystal with silicon same mono and shield\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/08 14:45

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S73	192	("3389024"   "3783049"		US-PGPUB;	OR	ON	2006/08/08 15:29	
	·	1"4059461"   "4068020"		USPAT;				
		"4174217"   "4226898"		USOCR				
		"4271422"   "4277884"		•	5			
			"4331709"		1			
		1"4379020"   "4409724"	•					
	]	"4472458"   "4481121"	•				•	
	}	"4544418"   "4546376"	•					
		"4634473"   "4735824"			į			
	i	"4911781"   "4959247"						
		"4996077"   "4996523"						
		1"5075259"   "5089441"						
		"5145808"   "5147826"						
		"5200630"   "5221423"	•					
			"5262350"					
		1 "5262654"   "5275851"						
		1"5289030"   "5296405"						
		1"5308998"   "5313075"						
		"5354697"   "5358907"						
		"5387530"   "5403772"						
		"5426064"   "5470763"	•					
		"5481121"   "5488000"						
		"5501989"   "5504019"						
		"5508533"   "5529937"	•	,				
	·	"5531182"   "5534716"	"5543352"					
		"5543636"   "5550070"						
		"5569610"   "5569936"	•					,
		"5580815"   "5585291"			}			
		"5591988"   "5595923"	•					
		"5604360"   "5605846"	"5606179"					
		"5608232"   "5612250"	"5614426"					
		"5614733"   "5616506"		Ì				
		"5620910"   "5621224"	•					
		"5624851"   "5637515"	"5639698"					
		"5643826"   "5646424"			j			
		"5656825"   "5661311"	•					
		"5677549"   "5684317"	"5684365"					
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		("5756364"   "5763899" 						
		"5782665"   "5786796"						
		"5808321"   "5811327"						
		"5821138"   "5821560"						
		"5828429"   "5838508"						
			"5882960"					
		"5888858"   "5895933"	"5899547"			,		
	1	"5922125"   "5929464"						
		"5933205"   "5940732"	"5949107"					
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	ł	"6013929"   "6031249"						
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S74	40	("5353133"   "5488236"   "5574475"   "5648792").PN. OR ("5808595"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/08 15:43
S75	2	("6,433,767") PN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/08 15:43
S76	2	("6818921").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/05 10:02
S77	4	"20030207545"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/05 09:57
S78	2	("6127702").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/05 10:42
S79	2	("6,583,440").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/05 10:02

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